

## FNK P-Channel Enhancement Mode Power MOSFET

### Description

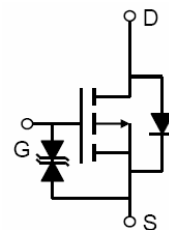
The FNK10P170K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

### General Features

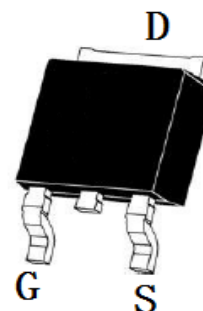
- $V_{DS} = -100V, I_D = -13A$   
 $R_{DS(ON)} < 200m\Omega @ V_{GS} = -10V$  (Typ: 170m $\Omega$ )
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low on-resistance

### Application

- Power switch
- DC/DC converters



Schematic diagram



TO-252 -2L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK10P170K	FNK10P170K	TO-252-2L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-13	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-9.2	A
Pulsed Drain Current	$I_{DM}$	-30	A
Maximum Power Dissipation	$P_D$	40	W
Derating factor		0.32	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	67.5	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

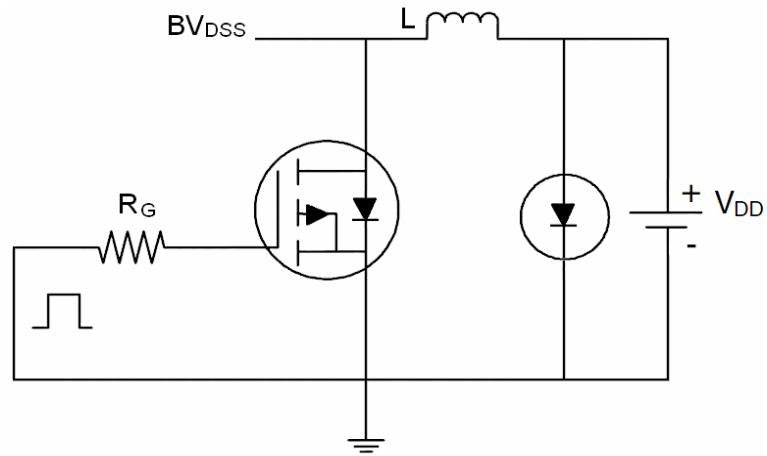
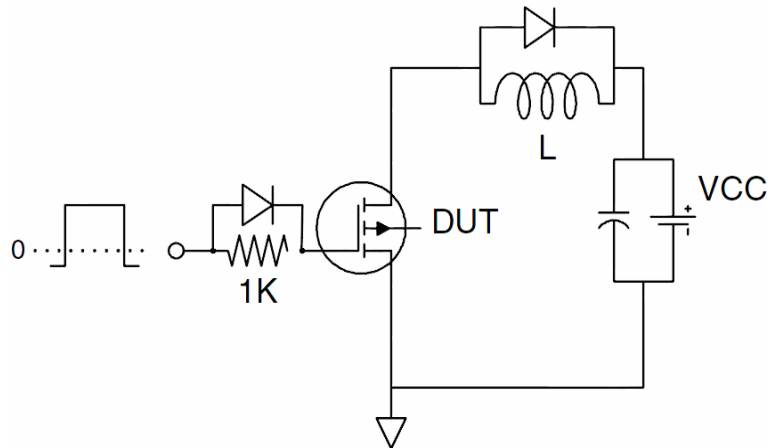
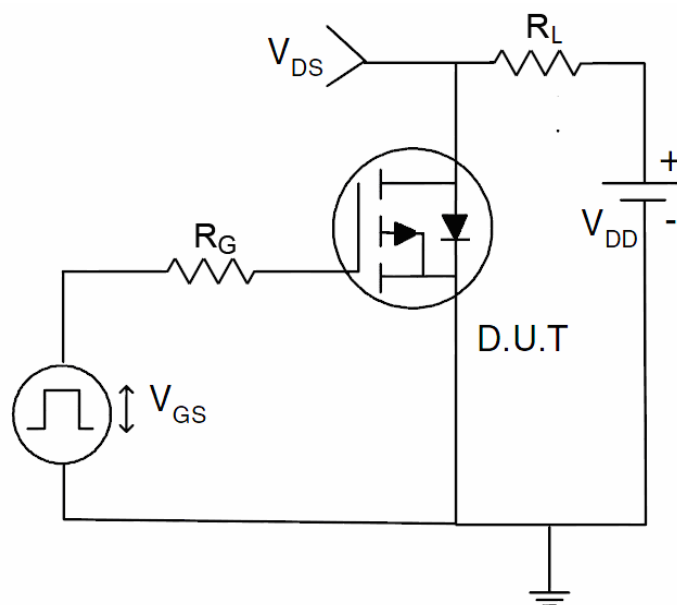
Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta jc}$	3.13	$^{\circ}\text{C/W}$
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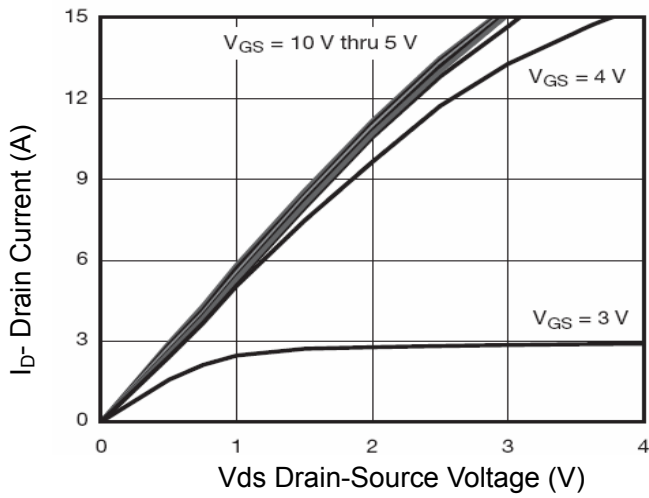
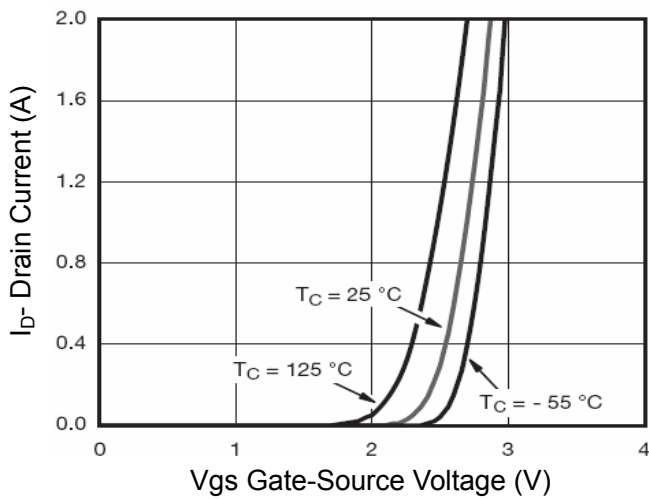
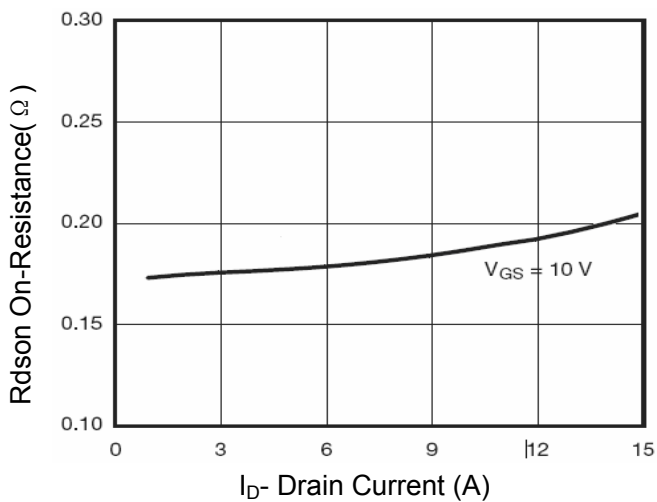
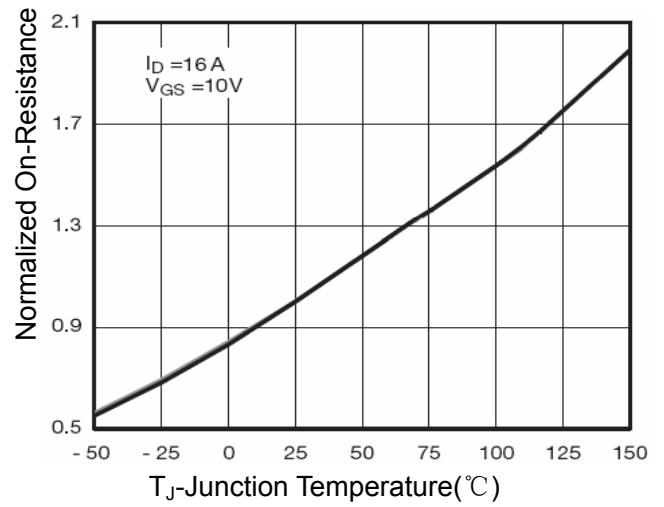
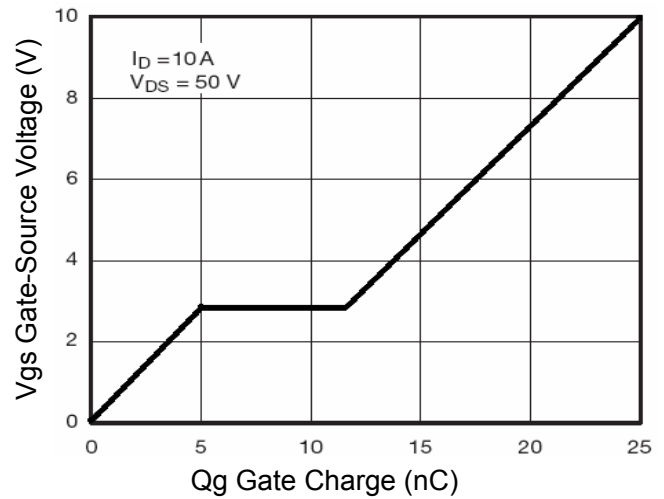
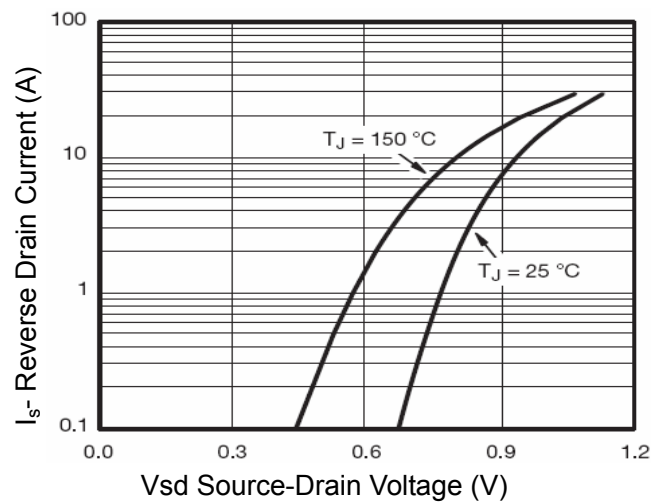
## Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

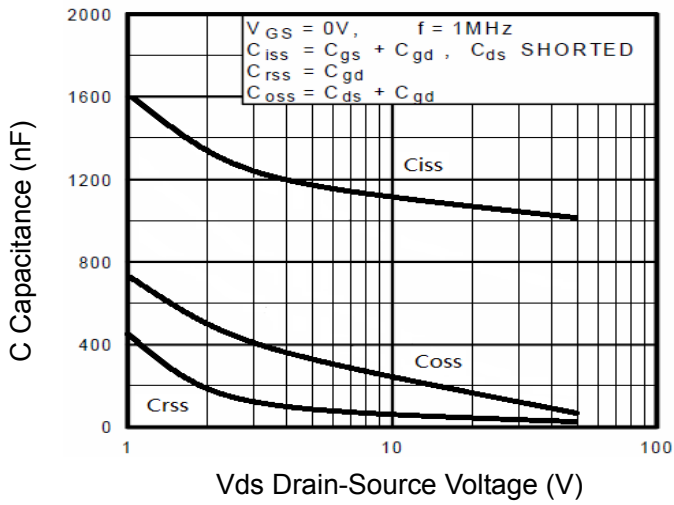
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 10$	$\mu A$
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-16A$	-	170	200	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-5A$	12	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1115	-	PF
Output Capacitance	$C_{oss}$		-	80	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	40	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-10A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	14	-	nS
Turn-on Rise Time	$t_r$		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	$t_f$		-	18	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-50V, I_D=-10A,$ $V_{GS}=-10V$	-	25	-	nC
Gate-Source Charge	$Q_{gs}$		-	5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_S$	-	-	-	-13	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = -10A$	-	35	-	nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$ (Note 3)	-	46	-	nC

## Notes:

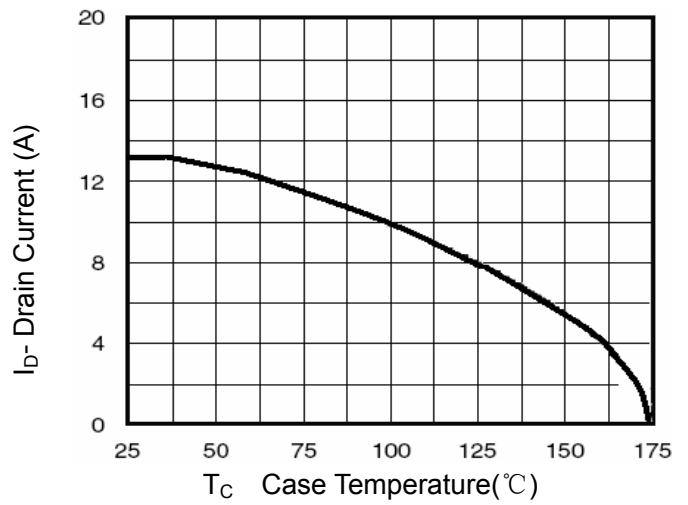
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $E_{AS}$  condition:  $T_J=25^{\circ}\text{C}, V_{DD}=-50V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

**Test Circuit**
**1) E<sub>AS</sub> Test Circuit**

**2) Gate Charge Test Circuit**

**3) Switch Time Test Circuit**


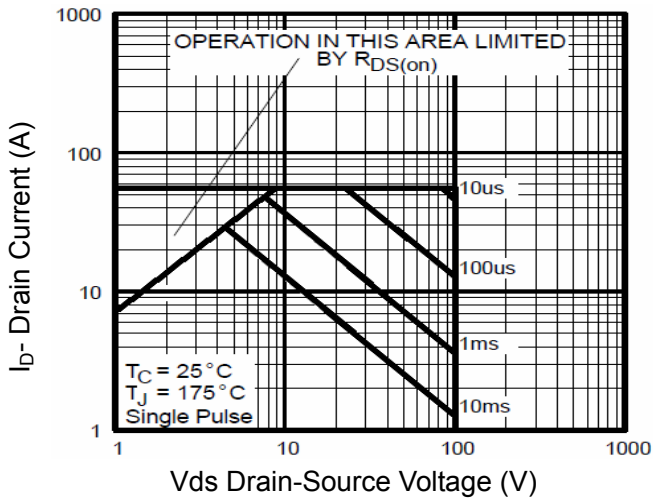
**Typical Electrical and Thermal Characteristics (Curves)**

**Figure 1 Output Characteristics**

**Figure 2 Transfer Characteristics**

**Figure 3 Rdson- Drain Current**

**Figure 4 Rdson-Junction Temperature**

**Figure 5 Gate Charge**

**Figure 6 Source- Drain Diode Forward**



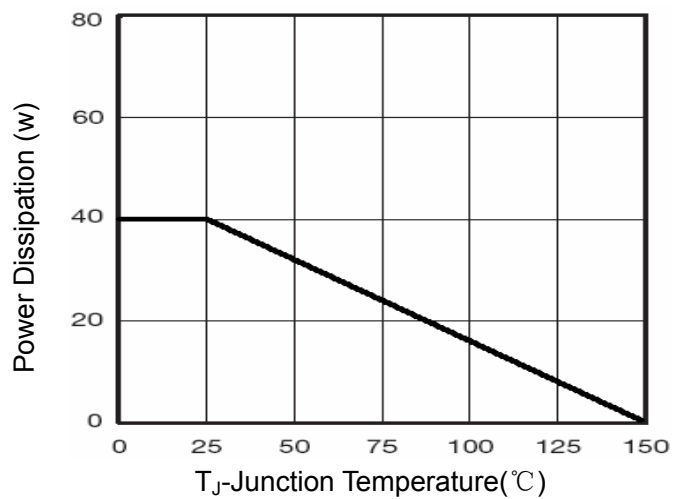
**Figure 7 Capacitance vs Vds**



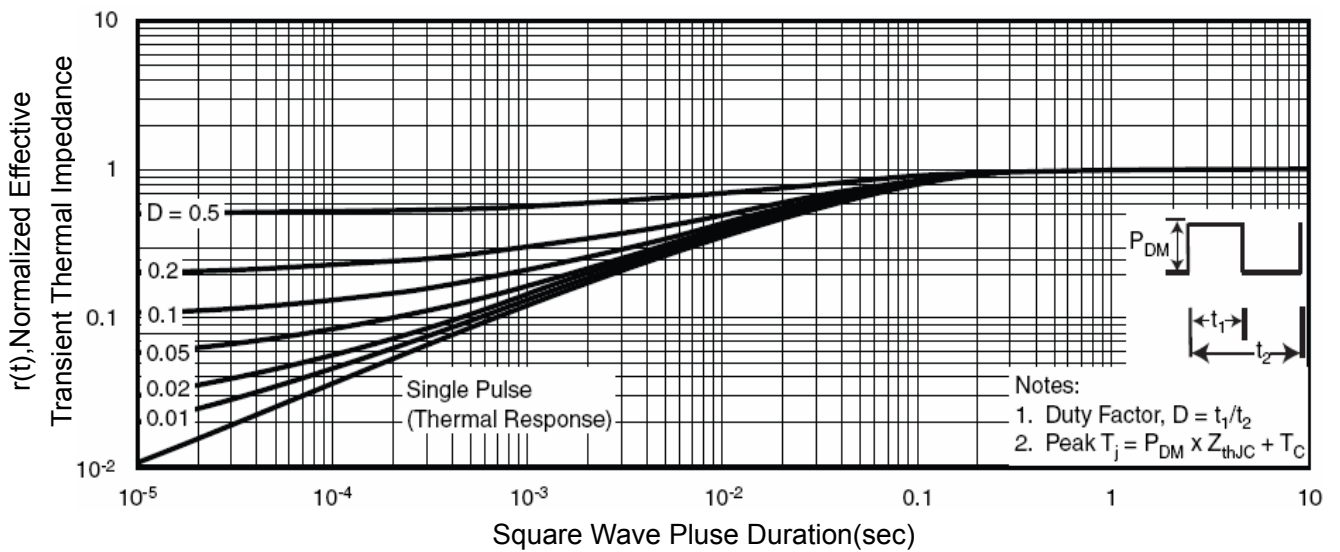
**Figure 9 Drain Current vs Case Temperature**



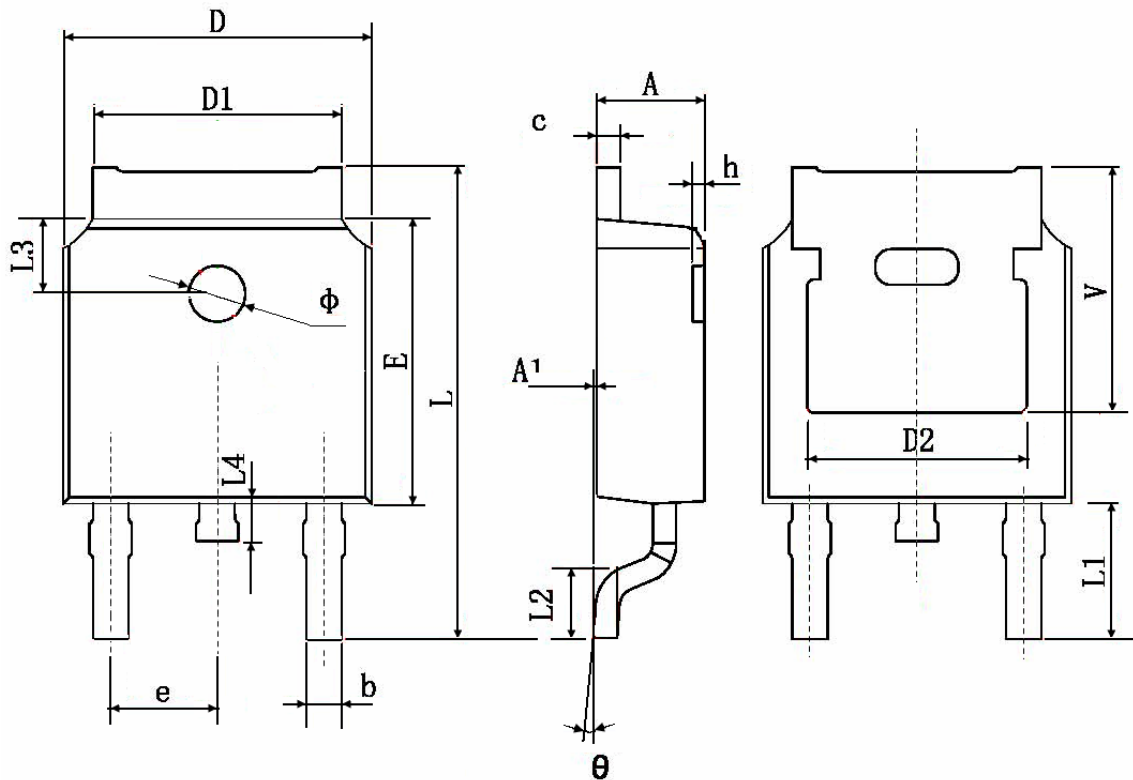
**Figure 8 Safe Operation Area**



**Figure 10 Power De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-252 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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